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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/813,330	03/30/2004	Jong-myeong Lee	5649-1205	5124
20792 7	7590 02/27/2006		EXAMINER	
MYERS BIGEL SIBLEY & SAJOVEC			EVERHART, CARIDAD	
PO BOX 37428 RALEIGH, NC 27627			ART UNIT	PAPER NUMBER
			2891	
			DATE MAILED: 02/27/2006	

Please find below and/or attached an Office communication concerning this application or proceeding.

	Application No.	Applicant(s)		
	10/813,330	LEE ET AL.		
Office Action Summary	Examiner	Art Unit		
	Caridad M. Everhart	2891		
The MAILING DATE of this communication app Period for Reply	ears on the cover sheet with the c	orrespondence address		
A SHORTENED STATUTORY PERIOD FOR REPLY WHICHEVER IS LONGER, FROM THE MAILING DA  - Extensions of time may be available under the provisions of 37 CFR 1.13 after SIX (6) MONTHS from the mailing date of this communication.  - If NO period for reply is specified above, the maximum statutory period w  - Failure to reply within the set or extended period for reply will, by statute, Any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b).	ATE OF THIS COMMUNICATION 36(a). In no event, however, may a reply be tim vill apply and will expire SIX (6) MONTHS from to cause the application to become ABANDONED	ely filed  he mailing date of this communication.  (35 U.S.C. § 133).		
Status				
Responsive to communication(s) filed on 12 December 2a) ☐ This action is FINAL. 2b) ☐ This 3) ☐ Since this application is in condition for alloware closed in accordance with the practice under E	action is non-final. nce except for formal matters, pro			
Disposition of Claims				
4) Claim(s) 1-20 is/are pending in the application.  4a) Of the above claim(s) is/are withdraw  5) Claim(s) is/are allowed.  6) Claim(s) 1-20 is/are rejected.  7) Claim(s) is/are objected to.  8) Claim(s) are subject to restriction and/or  Application Papers  9) The specification is objected to by the Examiner  10) The drawing(s) filed on is/are: a) access	vn from consideration. r election requirement.	:xaminer.		
Applicant may not request that any objection to the or Replacement drawing sheet(s) including the correction 11) The oath or declaration is objected to by the Extended 11.	drawing(s) be held in abeyance. See ion is required if the drawing(s) is obj	37 CFR 1.85(a). ected to. See 37 CFR 1.121(d).		
Priority under 35 U.S.C. § 119				
12) Acknowledgment is made of a claim for foreign a) All b) Some * c) None of:  1. Certified copies of the priority documents 2. Certified copies of the priority documents 3. Copies of the certified copies of the prior application from the International Bureau * See the attached detailed Office action for a list of	s have been received. s have been received in Application ity documents have been receive (PCT Rule 17.2(a)).	on No d in this National Stage		
Attachment(s)  1) Notice of References Cited (PTO-892)  2) D Notice of Draftsperson's Patent Drawing Review (PTO-948)	4) Interview Summary ( Paper No(s)/Mail Da	te		
3) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08)  Paper No(s)/Mail Date  5) Notice of Informal Patent Application (PTO-152)  6) Other:				

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Applicant's arguments with respect to claims 1-20 have been considered but are most in view of the new ground(s) of rejection.

## Claim Rejections - 35 USC § 103

The text of those sections of Title 35, U.S. Code not included in this action can be found in a prior Office action.

Claims 1,6,13,14, and 16-18 are rejected under 35 U.S.C. 103(a) as being unpatentable over Anma, et al. (US 2002/0072195A1) in view of Ebertseder, et al. (US 2002/0019880A1).

Anma, et al discloses a process which includes the steps of forming an insulation 1 shown in Fig. 20. Forming an opening shown in which is formed a titanium and TiN layer stack (paragraph 0070)(feature 4 in Fig. 20). A further layer of W is shown(feature 5)(paragraph 0079). The opening is filled with SOG(feature 10)(paragraph 0079) and polished back by CMP(paragraph 0104). Photoresist may be used instead of SOG(paragraph 0101). Layer 18 shown in Fig. 20 is also insulation(paragraph 0114). The upper surface of metal is removed by CMP(Fig. 21).

Anma, et al is silent with respect to the further steps of filling the trench and polishing the fill layer.

Ebertseder, et al discloses that an alignment mark trench is filled with metal(paragraph 0031) and planarized with CMP(paragraph 0031).

It would have been obvious to one of ordinary skill in the art at the time of the invention to have combined the steps taught by Ebertseder, et al and the process taught

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by Anma, et al because Anma, et al discloses a method for forming an alignment marking trench, and the steps of filling and planarizing would follow the steps taught by Anma, et al.

Claims 2-5,7-12, 19, and 20 are rejected under 35 U.S.C. 103(a) as being unpatentable over Anma, et al in view of Ebertseder, et al as applied to claim 1 above, and further in view of Ho, et al. (US 6,645,851B1).

Anma, et al in view of Ebertseder, et al is silent with respect to dual damascene.

Ho et al discloses that the method of forming a damascene pattern using sacrificial material may also be applied to dual damascene patterns (col. 3, lines 28-38), and dual damascene patterns have a via hole connected to a trench pattern above the via opening. The method disclosed by Ho, et al B uses a removable photoresist layer (col. 10, lines 59-62). The photoresist is etched back using developer(col. 4, lines 20-23). The photoresist may be removed using ashing(col. 4, lines 38-43). With respect to the relative etch rates, it is well known that the etch rates of oxide and photoresist are different.

It would have been obvious to one of ordinary skill in the art at the time of the invention to have combined the teaching of Ho, et al with the process taught by Anma, et al in order to obtain the benefits of the protection of the layers in the damascene structure in the same way as the layers of the alignment mark trench taught by Anma et al in view of Ebertseder, et al.

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Claim 15 is rejected under 35 U.S.C. 103(a) as being unpatentable over Anma, et al in view of Ebertseder, et al and further in view of Ho, et al as applied to claim 14 above, and further in view of Nishimura, et al.

Anma, et al in view of Ebertseder, et al and further in view of Ho, et al does not teach the reflow step.

Nishimura et al discloses reflow of Al in a via will increase the quality of the filling by having no void in the opening(page 171, last paragraph). Nishimura discloses the flowing of the aluminum in a via opening(page 171, second paragraph).

It would have been obvious to one of ordinary skill in the art at the time of the invention to have flowed the Al as taught by Nishimura, et al in the damascene structure taught by Anma, et al in view of Ebertseder, et al and further in view of Ho, et al in order to avoid the formation of a void in the openings.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Caridad M. Everhart whose telephone number is 571-272-1892. The examiner can normally be reached on Monday through Fridays 7:30-4:00.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, B. Baumeister can be reached on 571-272-1722. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

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Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

CARIDAD EVERHAFI PRIMARY EXAMINED

C. Everhart 2-14-2006